

2SD2108

Silicon NPN Triple Diffused
Low Frequency Power Amplifier

Absolute Maximum Ratings (Ta = 25°C)

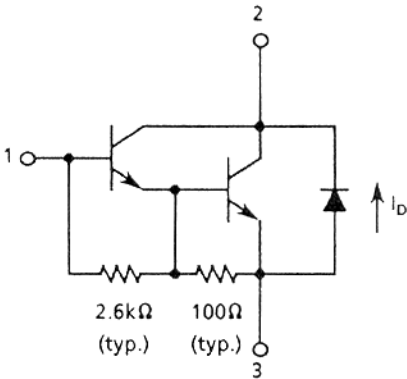
Item	Symbol	Rating	Unit
Collector to base voltage	V _{CBO}	80	V
Collector to emitter voltage	V _{CEO}	80	V
Emitter to base voltage	V _{EBO}	7	V
Collector current	I _C	8	A
Collector peak current	i _{C(peak)}	12	A
Collector power dissipation	P _C	2	W
	P _C ⁻¹	25	
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C
C to E diode forward current	I _D ⁻¹	8	A

Note: 1. Value at T_C = 25°C.

TO-220FM



- 1. Base
- 2. Collector
- 3. Emitter



Electrical Characteristics (Ta = 25°C)

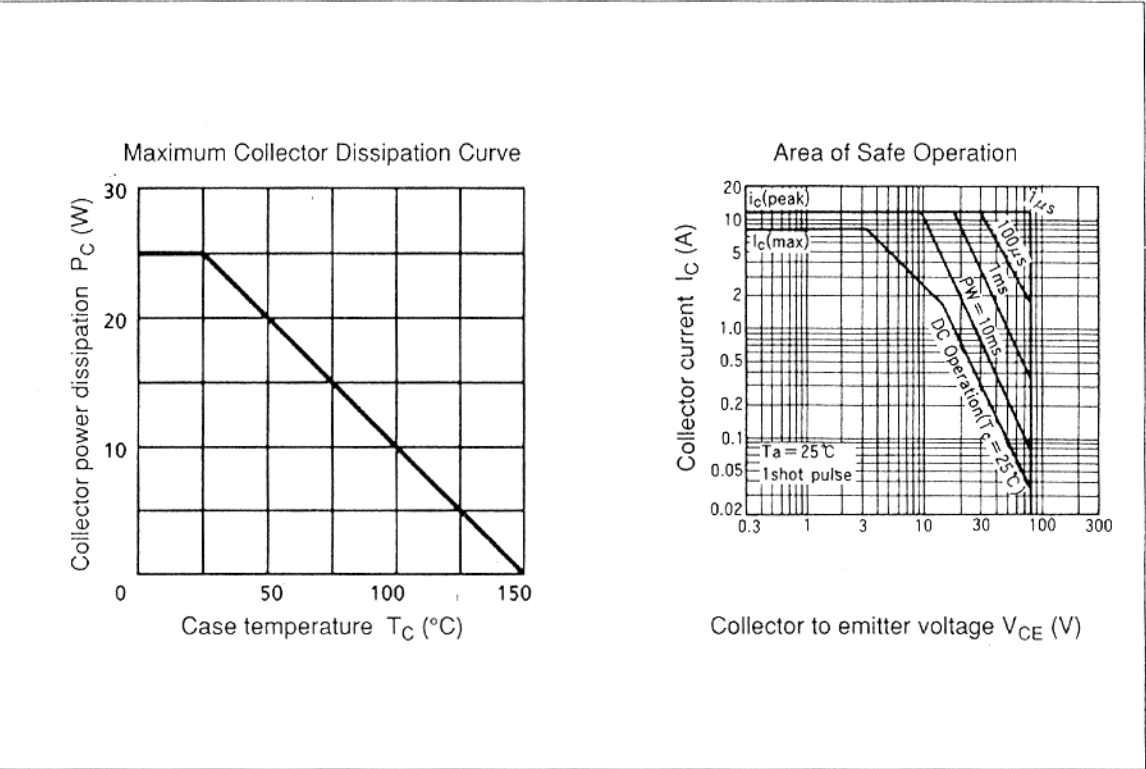
Item	Symbol	Min	Typ	Max	Unit	Test condition
Collector to base breakdown voltage	V _{(BR)CBO}	80	—	—	V	I _C = 0.1 mA, I _E = 0
Collector to emitter breakdown voltage	V _{(BR)CEO}	80	—	—	V	I _C = 25 mA, R _{BE} = ∞
Emitter to base breakdown voltage	V _{(BR)EBO}	7	—	—	V	I _E = 50 mA, I _C = 0
Collector cutoff current	I _{CBO}	—	—	10	μA	V _{CB} = 65 V, I _E = 0
	I _{CEO}	—	—	10		V _{CE} = 65 V, R _{BE} = ∞
DC current transfer ratio	h _{FE}	1000	—	20000		V _{CE} = 3 V, I _C = 4 A ⁻¹
Collector to emitter saturation voltage	V _{CE(sat)1}	—	—	1.5	V	I _C = 4 A, I _B = 8 mA ⁻¹
	V _{CE(sat)2}	—	—	3.0		I _C = 8 A, I _B = 80 mA ⁻¹

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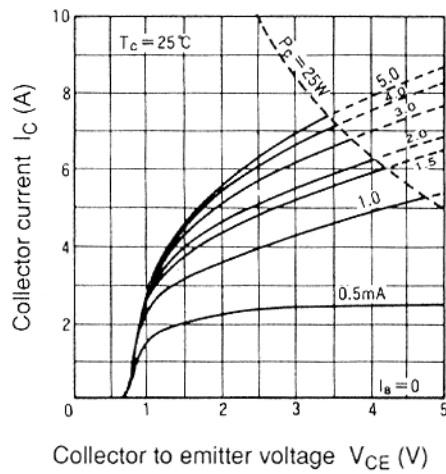
Electrical Characteristics (Ta = 25°C) (cont)

Item	Symbol	Min	Typ	Max	Unit	Test condition
Base to emitter saturation voltage	$V_{BE(sat)1}$	—	—	2.0	V	$I_C = 4\text{ A}, I_B = 8\text{ mA}^1$
	$V_{BE(sat)2}$	—	—	3.5		$I_C = 8\text{ A}, I_B = 80\text{ mA}^1$
C to E diode forward voltage	V_D	—	—	3.0	V	$I_D = 8\text{ A}^1$

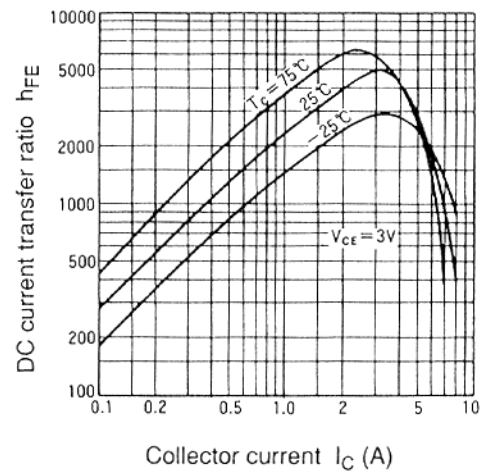
Note: 1. Pulse Test.
See switching characteristic curve of 2SD1604.



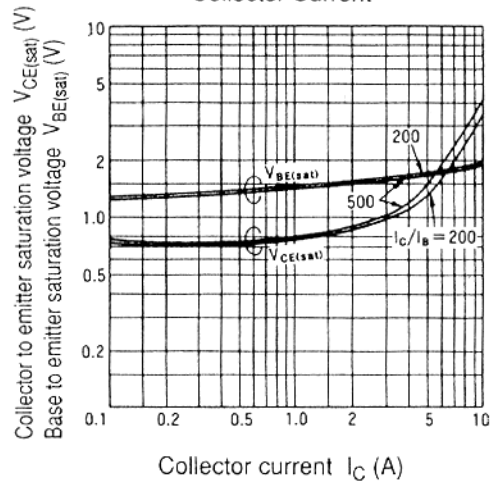
Typical Output Characteristics



DC Current Transfer Ratio vs. Collector Current



Saturation Voltage vs. Collector Current



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